ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

SEMICONDUCTOR DEVICE AND SEMICONDUCTOR SUBSTRATE, AND METHOD OF FABRICATING THE SAME

Application Number:

Confirmation Number:

First Named Applicant:

Masahiro ISHIDA

Attorney Docket Number:

28569,4136

Art Unit:

2811

Examiner:

Sara W. Crane

Search string:

(6111277 or 6337233 or 5834325 or 6121634 or 6153010 or 6015979 or 6051849

or 6177688 or 5285086 or 5032893 or 5294808 or 5208182).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

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Signature

Examiner Name	Date
CRANE	12/2004

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